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# FOR USE BY ELECTRICIANS OVERSEAS :

**最新トランジスタ規格表** (New Transistor Manual) lists all the transistors registered with the Electronic Industries Association of Japan (EIAJ), arranged in a manner easy to look up. We hope that you will make full use of the data provided in this manual by referring to the Japanese-English translation key given below.

型名	社名	用途	構造	最大定格 ( $T_c=25^\circ\text{C}$ )					電気的特性 ( $T_c=25^\circ\text{C}$ )										外形	備考	
				$V_{ce0}$ (V)	$V_{be0}$ (V)	$I_c$ (mA)	$P_c$ (mW)	$T_c$ ( $^\circ\text{C}$ )	$I_{c0}$ 最大値 ( $\mu\text{A}$ )	直流又はパルス $h_{FE}$		バイアス		$h_{FE}$	$h_{ie}$ $h_{ie}^*$ ( $\Omega$ )	$h_{re}$ $h_{re}^*$ ( $\times 10^{-4}$ )	$h_{oe}$ $h_{oe}^*$ ( $\mu\text{S}$ )	$f_{\alpha b}$ $f_{\alpha b}^*$ (Mc)			$C_{ob}$ (pF)
1	2	3	4	5					6		7		8				9	10		11	12

- 1 TYPE NUMBER
- 2 ORIGINAL MANUFACTURER
- 3 USES
- 4 MATERIAL AND STRUCTURE
- 5 MAXIMUM RATINGS
- 6  $I_{CBO}$  MAXIMUM VALUE AND  $V_{CB}$  VALUE (CRITERIA FOR MEASURING  $I_{CBO}$ )
- 7 STANDARD VALUE OF DC/PULSE  $h_{FE}$  AND  $V_{CE}$ ,  $I_C$  (CRITERIA FOR MEASURING DC/PULSE  $h_{FE}$ )
- 8 STANDARD VALUE OF  $h$  PARAMETERS AND BIAS  $V_{CB}$ ,  $I_E$  (CRITERIA FOR MEASURING  $h$  PARAMETERS)

- \* INDICATES VALUE IN GROUNDED-BASE OPERATION, OTHERWISE VALUE IN EMITTER-GROUNDED OPERATION.
- 9  $f_{\alpha b}$  OF RF CHARACTERISTIC, EXCEPT IN CASE OF \* WHICH INDICATES VALUE OF  $f_T$ .
- 10  $C_{ob}$  AND  $r_{bb'}$  OF RF CHARACTERISTICS EXCEPT IN CASE OF \* IN  $r_{bb'}$  COLUMN WHICH INDICATES VALUE OF  $h_{ie}$  (real)
- 11 OUTLINE
- 12 REMARKS

:とコンプリ: COMPLEMENTARY TO .....

型名	社名	用途	構造	最大定格 (T <sub>a</sub> = 25°C)					電 気 的 特 性 (T <sub>a</sub> = 25°C)												外形	備考			
				V <sub>CB0</sub> (V)	V <sub>EBO</sub> (V)	I <sub>C</sub> (mA)	P <sub>C</sub> (mW)	T <sub>J</sub> (°C)	I <sub>CB0</sub> 最大値		直流又はパルス		hFE		バイアス		h <sub>FE</sub> h <sub>FS</sub> *	h <sub>ic</sub> h <sub>is</sub> * (Ω)	h <sub>re</sub> h <sub>rb</sub> * (×10 <sup>-4</sup> )	h <sub>or</sub> h <sub>ob</sub> * (μU)			f <sub>ob</sub> f <sub>T</sub> * (Mc)	C <sub>ob</sub> (pF)	r <sub>bb'</sub> h <sub>i'(real)</sub> * (Ω)
									(μA)	V <sub>CB</sub> (V)	V <sub>CE</sub> (V)	I <sub>C</sub> (mA)	V <sub>CB</sub> (V)	I <sub>E</sub> (mA)	h <sub>FE</sub>	I <sub>E</sub> (mA)									
2SC654	日電	RF	Si.E	40	3	300	800	150	1	35				15	-50	80					650	2.9	21*	85B	
" 655	松下	RF.AF.PA	Si.EP	10	2	10	75	125	1	10	400	5	2	5	-2	250	3500	2.5	35	80*	4.5	70	34		
" 656	"	RF	"	10	2	5	50	125	1	10				10	-5	130				550*	1.5	C <sub>e</sub> r <sub>bb'</sub> 80pS	34		
* " 657	ソニー	RF.Conv.Mix Osc	Si.DB	18		30	150	120	0.2	15	50	10	4	6	-1	50					500*	1.1	C <sub>e</sub> r <sub>bb'</sub> 15pS	38	
* " 658	三菱	"	"	25	4	20	150	150	1	12	60	6	1	6	-1	60				550*	1.5	C <sub>e</sub> r <sub>bb'</sub> 30pS	8 A		
* " 659	"	"	"	25	4	20	150	150	1	12	60	6	1	6	-1	60				400*	1.5	C <sub>e</sub> r <sub>bb'</sub> 40pS	8 A		
* " 660	"	RF.Conv Mix	Si.P	25	4	20	150	150	0.5	20	60	10	3	10	-3	60				600*	1	C <sub>e</sub> r <sub>bb'</sub> 3pS	11A	フワード AGC	
* " 661	"	"	"	25	4	20	150	150	0.5	20	60	10	3	10	-3	60				600*	1	C <sub>e</sub> r <sub>bb'</sub> 4pS	11A	フワード AGC	
* " 662	"	RF.Conv Mix.Osc	Si.EP	25	2	20	150	150	0.5	10				6	-2	40				800*	1	C <sub>e</sub> r <sub>bb'</sub> 4pS	9		
* " 663	"	"	"	25	2	20	150	150			10~ 300	10	10							900*	1.4	C <sub>e</sub> r <sub>bb'</sub> 5pS	11A		
* " 664	日立	PA.SW	Si.T	100	5	5 A	50 W (T <sub>e</sub> =25°C)	150	1mA	30	80	5	1 A											102	
* " 665	"	"	"	130	6	7 A	50 W (T <sub>e</sub> =25°C)	150	200	30	30~130	5	5 A											102	
* " 666																									
* " 667																									
* " 668	三洋	RF.Conv. Mix.	Si.TP	25	3	30	150	125	1	10	25~560	6	1	6	-1					600*	C <sub>rr</sub> 0.75	C <sub>e</sub> r <sub>bb'</sub> <30pS	92		
" 669	ソニー	PA	Si.E	30	5	2 A	1 W	175	5	25	70	2	100	10	-50	70				65*	18		181		
* " 669A	"	"	Si.EMe	100	6	3 A	10 W (T <sub>e</sub> =25°C)	175	3	25	170~400	2	100	10	-50	70				65*	35		181		
" 670																									
" 671																									
" 672																									
" 673																									
* " 674	三洋	RF.Conv. Mix.	Si.TP	25	4	30	150	125	1	10	40~320	6	1	6	-1					600*	C <sub>rr</sub> 0.75	C <sub>e</sub> r <sub>bb'</sub> 17pS	92		
" 675	芝電	SW	Si.Me	250	6	7 A	50 W (T <sub>e</sub> =25°C)	180	10	30	30	10	0.5A											102	
" 676	"	"	"	200	6	7 A	50 W (T <sub>e</sub> =25°C)	180	10	30	30	10	0.5A											102	
" 677	"	"	"	150	6	7 A	50 W (T <sub>e</sub> =25°C)	180	30	30	40	10	0.5A											102	
" 678	"	"	"	100	6	7 A	50 W (T <sub>e</sub> =25°C)	180	100	30	40	10	0.5A											102	
* " 679	日立	PA	Si.T	300	6	2 A	30 W (T <sub>e</sub> =25°C)	175	1	30	60	10	20	10	-200	190				20*	75	20	153		
* " 680	"	"	"	200	6	2 A	12.5 W (T <sub>e</sub> =25°C)	150	1	30	180	10	200	10	-200	190				20*	75	20	153		
" 681	"	SW	"	200	5	6 A	50 W (T <sub>e</sub> =25°C)	150	I <sub>CBX</sub> 15mA	200														102	水平偏用
* " 682	"	RF	Si.P	20	3	20	180	175	0.1	10	60	10	2	10	-2	75	PG = 28dB (f = 45Mc)			550*	C <sub>rr</sub> 0.37		9	フワード AGC	